

➤ PRODUCT DATA SHEET

# MTS1 TEMP eco bare die

Thermal IR detector chip  
for temperature measurement



## Technical data

Technical parameter		Unit
Active area	0.7 x 0.7	mm <sup>2</sup>
Time constant <small>(10-90 %)</small>	typ. 40	ms
DC sensivity	typ. 45	V/W
Noise voltage	typ. 35	nV/Hz <sup>1/2</sup>
Noise equivalent power NEP	typ. 0.78	nW/Hz <sup>1/2</sup>
Specific dectivity D*	typ. 0.9*10 <sup>8</sup>	cmHz <sup>1/2</sup> /W
Resistance of thermopile	typ. 75 ± 25	kΩ
Wafer diameter	150 ± 0.3	mm
Wafer thickness	375 ± 15	µm
Chips per wafer	6000	pcs
Bond pad material	Aluminum	
Maximum operating temperature	-40 ... 100	°C
Maximum storage temperautre	-40 ... 100	°C

All values are tested in the laboratories only. Customers have to evaluate these parameters for their applications in advance.

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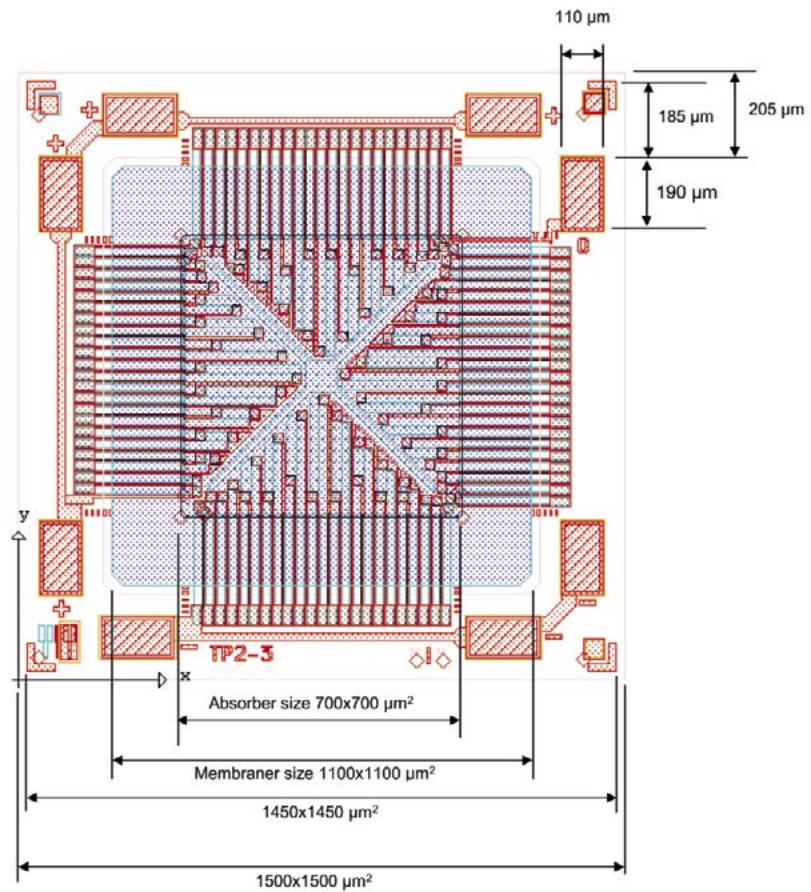


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Mechanical drawings

Top view



NOVA IR and CMOSIR are companies of Micro-Hybrid Electronic GmbH.